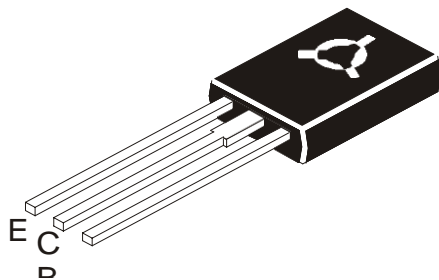


NPN EPITAXIAL SILICON POWER TRANSISTOR

MJE340



**TO126
Plastic Package**

For use in High Voltage General Purpose Applications

ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNIT
Collector Emitter Voltage	V_{CEO}	300	V
Collector Base Voltage	V_{CBO}	300	V
Emitter Base Voltage	V_{EBO}	3.0	V
Collector Current Continuous	I_C	500	mA
Power Dissipation @ $T_a=25^\circ\text{C}$ Derate above 25°C	P_D	1.25 10	W mW/ $^\circ\text{C}$
Power Dissipation @ $T_c=25^\circ\text{C}$ Derate above 25°C	P_D	20 0.16	W W/ $^\circ\text{C}$
Operating And Storage Junction Temperature Range	T_j, T_{stg}	- 65 to +150	$^\circ\text{C}$

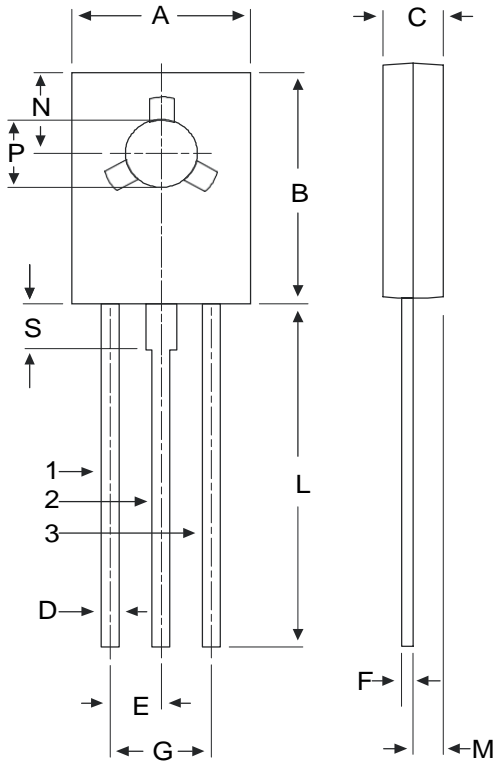
THERMAL CHARACTERISTICS

Junction to Ambient in free air	$R_{th(j-a)}$	100	$^\circ\text{C/W}$
Junction to Case	$R_{th(j-c)}$	6.25	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless specified otherwise)

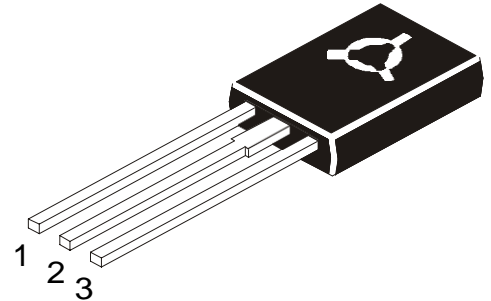
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Emitter Sustaining Voltage	$*V_{CEO(sus)}$	$I_C=1\text{mA}, I_B=0$	300		V
Collector Cut Off Current	I_{CBO}	$V_{CB}=300\text{V}, I_E=0$		100	μA
Emitter Cut Off Current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$		100	μA
DC Current Gain	h_{FE}	$I_C=50\text{mA}, V_{CE}=10\text{V}$	30	240	

TO-126 (SOT-32) Plastic Package



DI M	MI N	MAX
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.4	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	

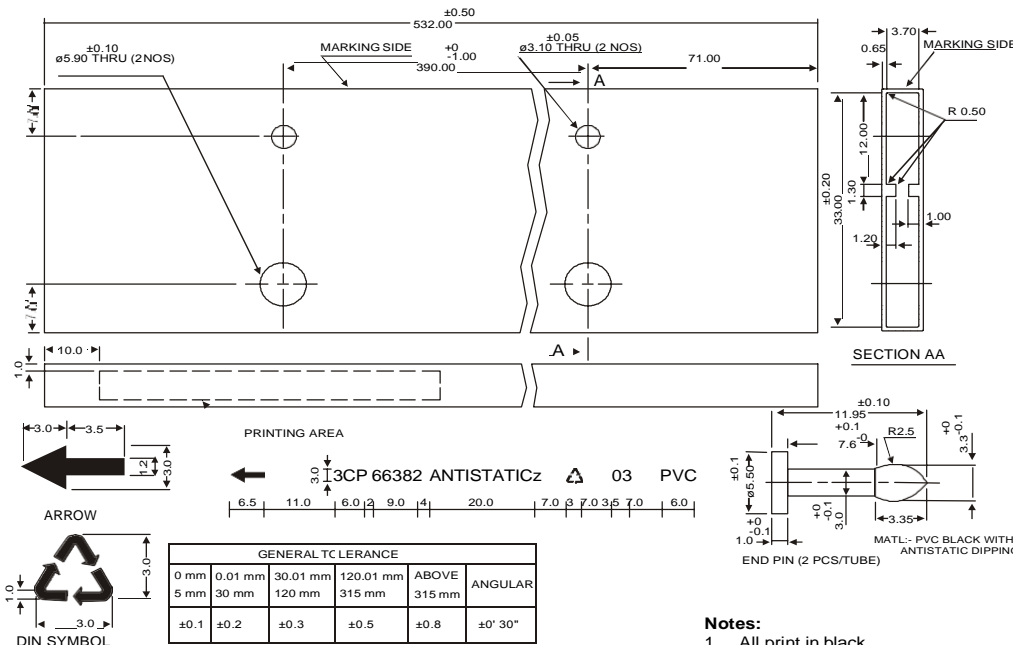
All dimensions in mm.



Pin Configuration

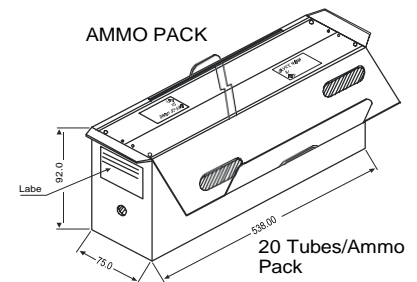
1. Emitter
2. Collector
3. Base

TO-126 TUBE PACKING



All dimensions in mm

- Notes:
1. All print in black.
 2. All text in Helvetia medium font.



Packing Details

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-126 Bulk	500 pcs/polybag	340 gm/500 pcs	3" x 7.5" x 7.5"	2K	17" x 15" x 13.5"	32K	31 kgs
TO-126 Tube	50 pcs/tube	73 gm/50 pcs	3" x 3.7" x 21.5"	1K	19" x 19" x 19"	10K	15 kgs

